SUPPORTING INFORMATION

The Role of Third Cation Doping on Phase Stability, Carrier Transport and Carrier Suppression in Amorphous Oxide Semiconductors

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EDS Measurements

X-ray energy dispersive spectroscopy (EDS) measurements to identify the concentration of a series of IAZO were made as a function of rf power (10, 20 and 30 W) for Al during co-sputtering while maintaining dc power (20 W) for IZO to incorporate Al into the IZO matrix. According to the EDS measurements, the concentration (wt.%) of Al in the IAZO films was determined to be 4, 8.9 and 16.7 wt.%.

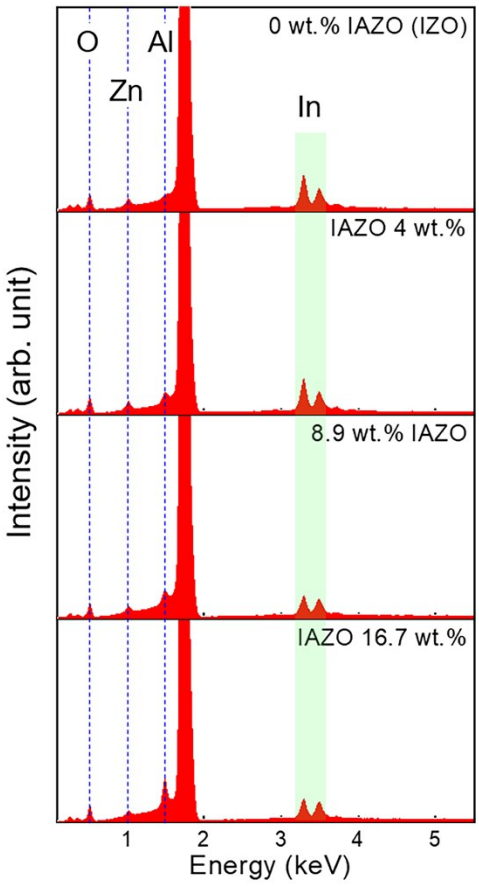

Figure S1. EDS elemental analysis to identify the concentration of Al in a series of IAZO films.